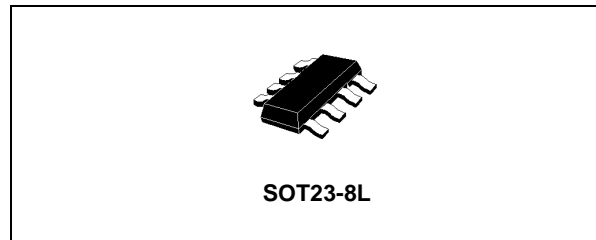


TRIPLE SCHMITT INVERTER

- HIGH SPEED: $t_{PD} = 3.0ns$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu A$ (MAX.) at $T_A = 25^\circ C$
- TYPICAL HYSTERESIS:
 $V_H = 800mV$ at $V_{CC} = 4.5V$
 $V_H = 500mV$ at $V_{CC} = 3.0V$
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 8mA$ (MIN) at $V_{CC} = 4.5V$
 $|I_{OH}| = I_{OL} = 4mA$ (MIN) at $V_{CC} = 3.0V$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $5.5V$
- IMPROVED LATCH-UP IMMUNITY



ORDER CODES

PACKAGE	T & R
SOT23-8L	74V2G14STR

Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.

Pin configuration and function are the same as those of the 74V2G04, but 74V2G14 has hysteresis on inputs.

This device can be used to interface 5V to 3V systems and it is ideal for portable applications like personal digital assistant, camcorder and all battery-powered equipment.

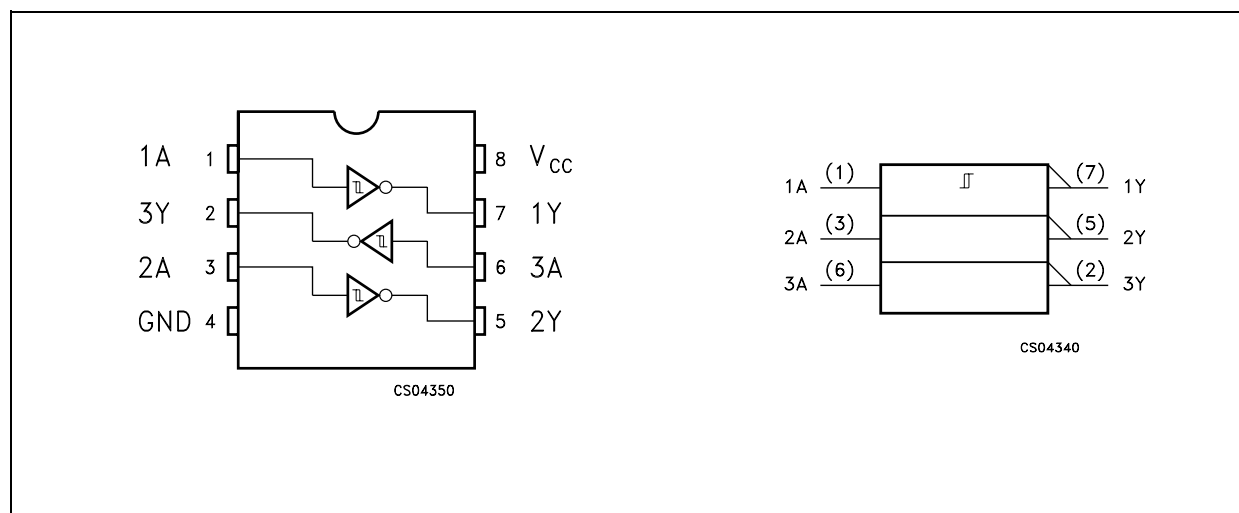
All inputs and outputs are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

DESCRIPTION

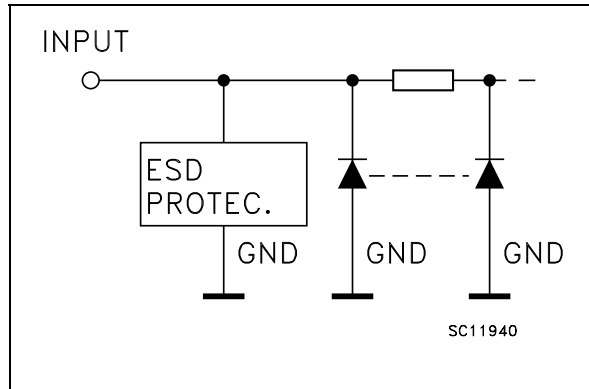
The 74V2G14 is an advanced high-speed CMOS TRIPLE SCHMITT TRIGGER INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME QND FUNCTION
1, 3, 6	1A, 2A, 3A	Data Inputs
7, 5, 2	1Y, 2Y, 3Y	Data Outputs
4	GND	Ground (0V)
8	V _{CC}	Positive Supply Voltage

TRUTH TABLE

nA	nY
L	H
H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage (see note 1)	-0.5 to +7.0	V
V _O	DC Output Voltage (see note 2)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	- 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

1) V_{CC}=0V

2) High or Low State

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _P	High Level Input Voltage	3.0				2.20		2.20		2.20	V
		4.5				3.15		3.15		3.15	
		5.5				3.85		3.85		3.85	
V _N	Low Level Input Voltage	3.0		0.90			0.90		0.90		V
		4.5		1.35			1.35		1.35		
		5.5		1.65			1.65		1.65		
V _H	Hysteresis Voltage	3.0		0.30		1.20	0.30	1.20	0.30	1.20	V
		4.5		0.40		1.40	0.40	1.40	0.40	1.40	
		5.5		0.50		1.60	0.50	1.60	0.50	1.60	
V _{OH}	High Level Output Voltage	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		V
		3.0	I _O =-50 μA	2.9	3.0		2.9		2.9		
		4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		
		3.0	I _O =-4 mA	2.58			2.48		2.4		
		4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output Voltage	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			1		10		20	μA
I _{OPD}	Power down Output Leakage Current	0	V _O = 5.5			0.5		5		10	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)	C _L (pF)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PLH} t _{PHL}	Propagation Delay Time	3.3(*)	15		3.7	7.0	1.0	8.0	1.0	9.0	ns
		3.3(*)	50		5.3	8.0	1.0	9.5	1.0	10.5	
		5.0(**)	15		3.0	5.0	1.0	6.0	1.0	7.0	
		5.0(**)	50		4.1	6.5	1.0	7.5	1.0	8.5	

(*) Voltage range is 3.3V ± 0.3V

(**) Voltage range is 5.0V ± 0.5V

CAPACITANCE CHARACTERISTICS

Symbol	Parameter	Test Condition	Value						Unit	
			T _A = 25°C			-40 to 85°C		-55 to 125°C		
			Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			12						pF

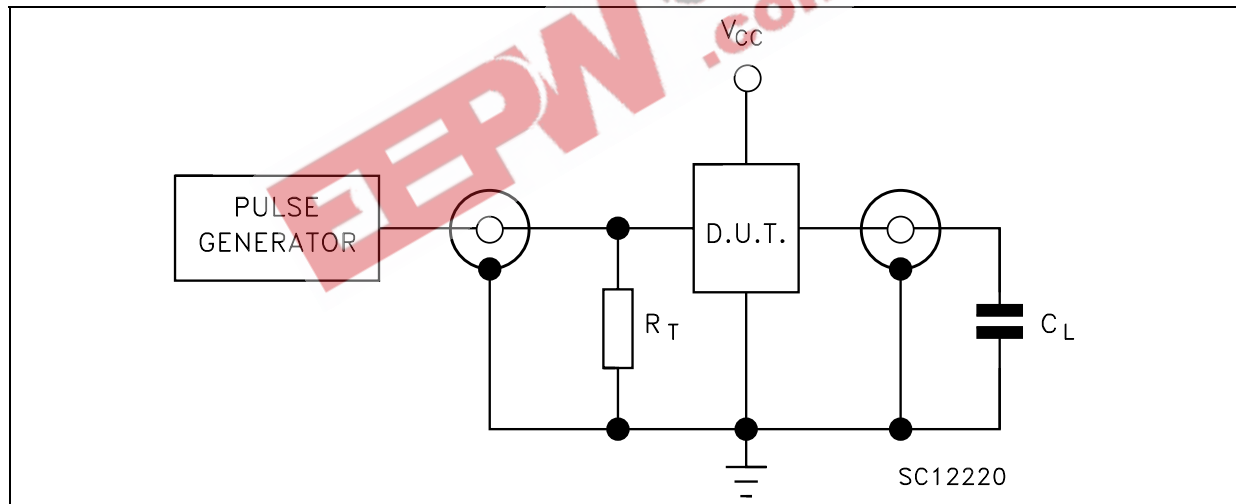
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/3$

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value		Unit
		V _{CC} (V)		T _A = 25 °C		
				Min.	Max.	
V _{OLP}	Dynamic Low Level Quiet Output (note 1)	5.0	C _L = 50pF V _{IL} = 0V, V _{IH} = 3.3V		0.8	V
V _{OLV}				-0.8		

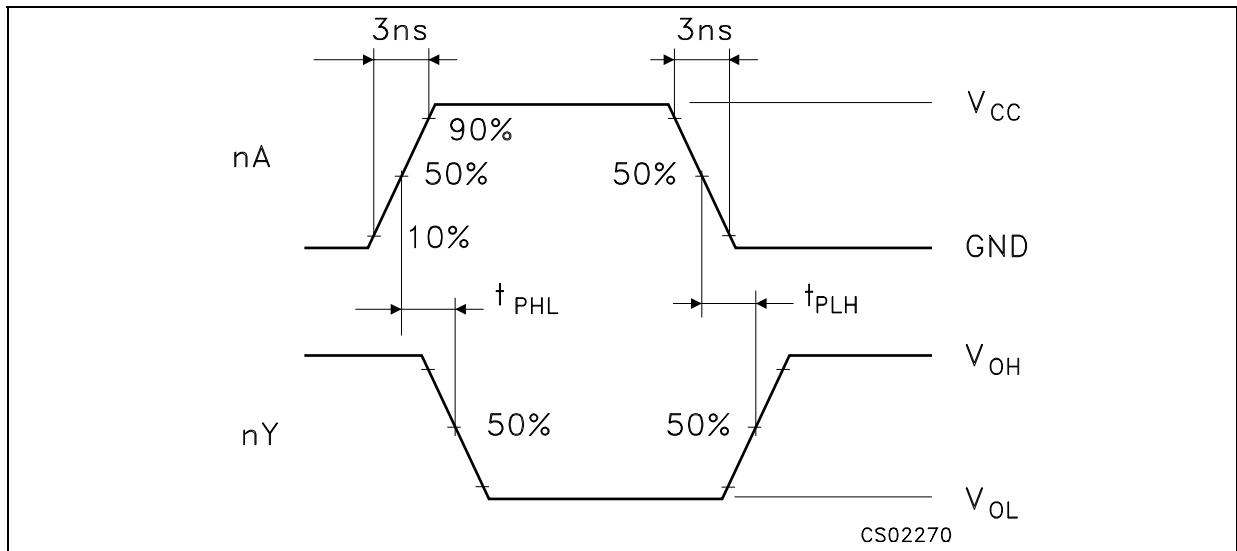
1) Number of output defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining outputs is measured in the LOW state.

TEST CIRCUIT



C_L = 15/50pF or equivalent (includes jig and probe capacitance)
R_T = Z_{OUT} of pulse generator (typically 50Ω)

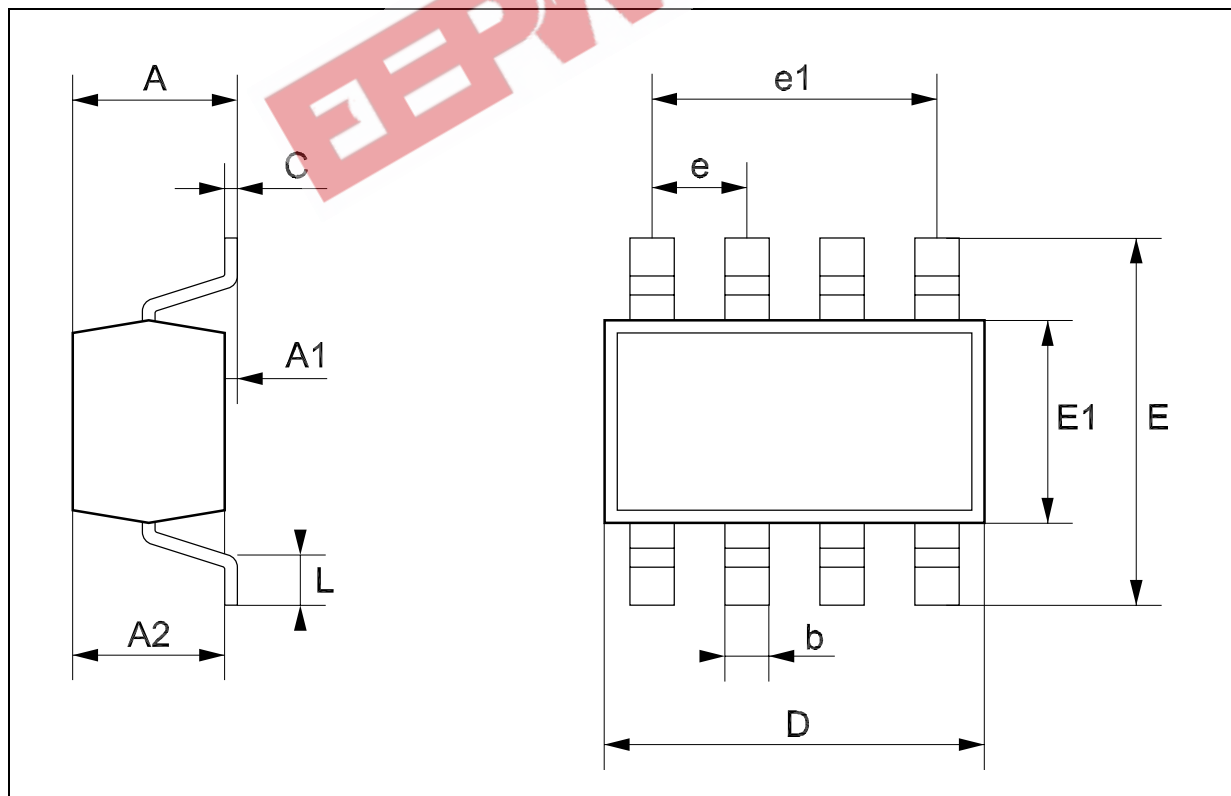
WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



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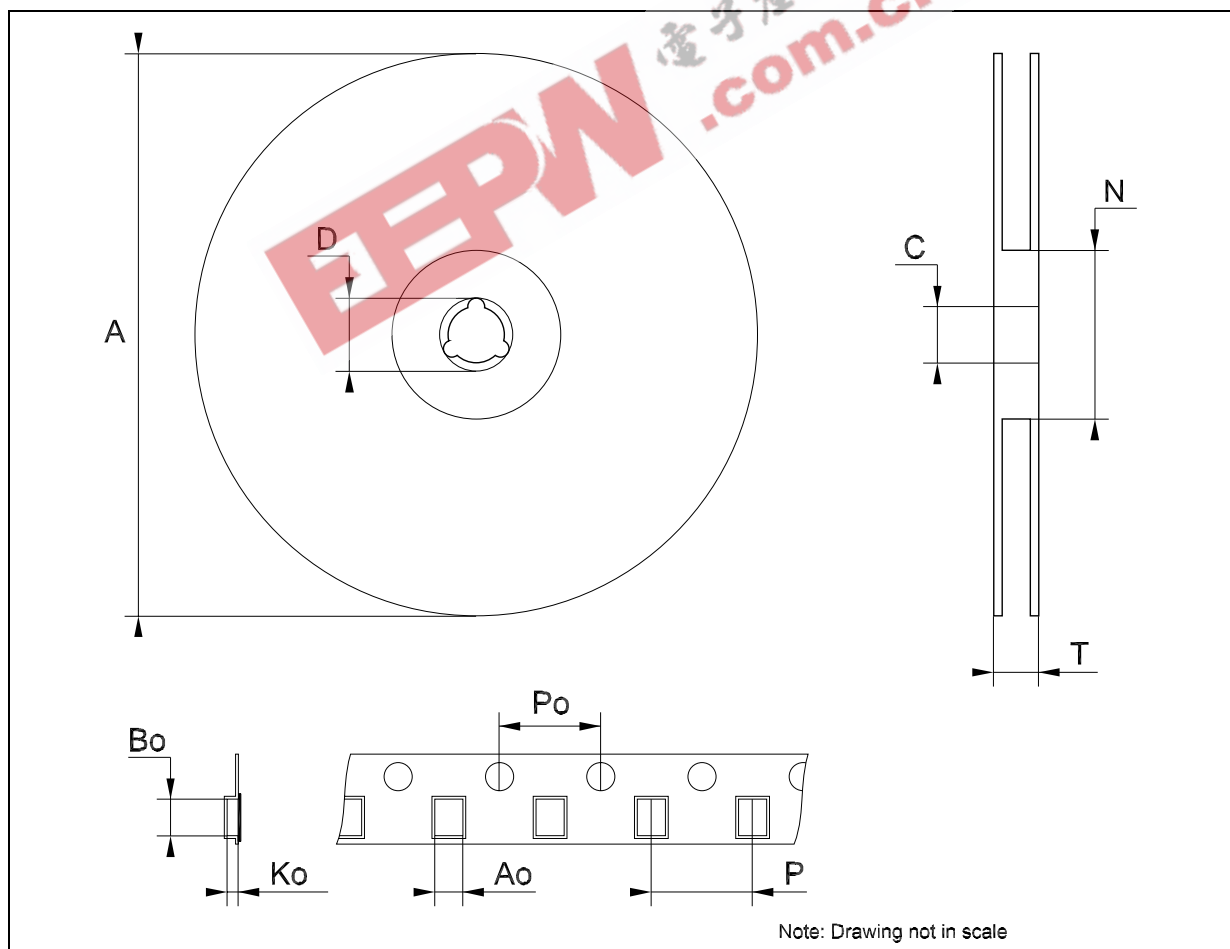
SOT23-8L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
e	0	.65		25.6		
e1		1.95		76.7		
L	0.35		0.55	13.7		21.6



Tape & Reel SOT23-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157	0.161



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